ABSTRACT OF THE DISCLOSURE

A process for producing a semiconductor substrate is provided which comprises providing a first member having a porous monocrystalline silicon layer and a nonporous monocrystalline silicon layer grown thereon, laminating the nonporous silicon layer of the first member onto a second member with interposition of an insulation layer provided on at least one lamination face of the first member and the second member, and removing the porous monocrystalline silicon layer by etching, wherein the nonporous monocrystalline silicon layer is grown at a low growth rate controlled such that the density of remaining pores on the crystal growth face is not more than 1000/cm^2 at the time when the nonporous silicon layer has grown to a thickness corresponding to the diameter of the pores of the porous monocrystalline silicon layer.

This Sheet Has Been Replaced



THIS SHEET HAS BEEN REPLACED